

FOR IMMEDIATE RELEASE

No. 2389

Product Inquiries:

Hideyuki Oto
High Frequency & Optical Semiconductor
Overseas Marketing Division
Tel +81-72-780-3835
Oto.Hideyuki@ak.MitsubishiElectric.co.jp
<http://www.mitsubishichips.com/>

Media Contact:

Travis Woodward
Public Relations Division
Mitsubishi Electric Corporation
Tel: +81-3-3218-2346
Travis.Woodward@eb.MitsubishiElectric.co.jp
<http://global.mitsubishielectric.com/news/>

**MITSUBISHI ELECTRIC ANNOUNCES SALE OF LOW NOISE GaAs
HEMT in Ka band ‘MGF4961B’**

Tokyo, August 1, 2006 – Mitsubishi Electric Corporation (President and CEO: Setsuhiro Shimomura) announced today it has developed a high gain version of a micro-X package High Electron Mobility Transistor (HEMT), highly suitable for low noise amplifiers in 18-20 GHz-band satellite broadcasting reception systems and Very Small Aperture Terminal (VSAT) systems. Shipment will begin in October 2006.

Sale Summary

Product	Model	Characteristic	Price	Release Date	Amount
Low Noise GaAs HEMT	MGF4961B	NF:0.7dB Gs:13.5dB (f=20GHz)	price of sample \$0.90	Oct. 20, 2006	500,000 /month

Aim of Sale

These transistors will mainly be used in the Ka band Direct Broadcast Satellite (DBS) and VSAT markets for low noise amplifiers in reception converters. The recent launch of the 20GHz(down link)/30GHz(up link) (Ka band) systems is expected to increase demand for HEMT, due to the expansion of transmission capacity in current satellite communication systems with the development of high-speed data link and Digital/High Definition broadcasts, etc. The market is demanding low price and high gain/low noise characteristic in high frequencies for the Ka band systems.

Mitsubishi Electric responded to this market demand by creating a high gain version of a micro-X package HEMT. This new HEMT has a transistor with a 3 dB gain over previous HEMT, achieved by optimization of the package structure. It will improve the cost performance of satellite communication equipments.

Product Characteristics

3 dB transmission gain over previous HEMT

By optimizing the package structure for Ka band, NF (noise figure) =0.7 dB, Gs (associated gain) =13.5 dB (f=20GHz, typical value), we achieved a 3 dB gain over previous HEMT.

Features

- Recommended bias condition: VDS=2V、ID=10mA
- Noise figure (NFmin.): 0.7dB (f=20GHz, typical)
- Associated gain (Gs): 13.5dB (f=20GHz, typical)

Use of standard micro-X package

An unchanged foot pattern from previous HEMT will make new product substitution easy.

About Mitsubishi Electric

With over 80 years of experience in providing reliable, high-quality products to both corporate clients and general consumers all over the world, Mitsubishi Electric Corporation (TSE:6503) is a recognized world leader in the manufacture, marketing and sales of electrical and electronic equipment used in information processing and communications, space development and satellite communications, consumer electronics, industrial technology, energy, transportation and building equipment. The company recorded consolidated group sales of 3,604 billion yen (US\$ 30.8billion*) in the fiscal year ended March 31, 2006. For more information visit <http://global.mitsubishielectric.com>

*At an exchange rate of 117 yen to the US dollar, the rate given by the Tokyo Foreign Exchange Market on March 31, 2006.

###